

# Heating of Two-Dimensional Holes in SiGe and the $B = 0$ Metal-Insulator Transition

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(November 3, 2018)

We study the resistivity vs. electric field dependence  $\rho(E)$  of a 2D hole system in SiGe close to the  $B = 0$  metal-insulator transition. Using  $\rho$  as a “thermometer” to obtain the effective temperature of the holes  $T_e(E)$ , we find that the  $\rho(E)$  dependence can be attributed to hole heating. The hole-phonon coupling involves weakly screened piezoelectric and deformation potentials compatible with previous measurements. The damping of the Shubnikov-de Haas oscillations gives the same  $T_e$  values. Thus the  $\rho(E)$  dependence and the  $E$ -field “scaling” do not provide additional evidence for a quantum phase transition (QPT). We discuss how to study, in general, true  $E$ -field scaling and extract the ratio of the QPT characteristic lengths.

PACS numbers: 71.30.+h, 63.20.Kr, 73.43.Nq

The recent observations of a metal-insulator transition (MIT) in two-dimensional (2D) electron or hole systems in high mobility silicon metal-oxide-semiconductor field effect transistors (Si-MOSFETs) [1,2] and in certain heterostructures [3–8] have triggered important experimental and theoretical efforts to understand the unexpected metallic behavior [8,9]. This consists in a decrease of the resistivity  $\rho$  for decreasing temperature  $T$ , at densities  $p_s$  larger than the critical density  $p_c$ . In contrast,  $d\rho/dT < 0$  on the insulating side of the MIT ( $p_s < p_c$ ). The extrapolated finite resistivity at  $T=0$  is in conflict with the scaling theory of localization for non-interacting particles which predicts localized states in 2D systems [10]. The MIT occurs for values of  $r_s$  (the ratio of a carrier pair Coulomb energy to the Fermi energy) much larger than one, suggesting the existence of a non-Fermi liquid due to strong interactions. The MIT could thus be the signature of a  $T=0$  quantum phase transition (QPT) between new metallic and insulating phases. However, for some systems, e.g.  $p$ -SiGe, it seems that the positive  $d\rho/dT$  is due to quasi-classical processes masking the usual weak localization which should appear again at low enough temperatures [9,11–13]. At present, the nature of the MIT is still a subject of ongoing discussions.

A striking feature of the MIT is that at low temperature, the dependence of  $\rho$  as a function of the electric field  $E$  is similar to  $\rho(T)$ , i.e.  $d\rho/dE < 0$  for  $p_s < p_c$  and  $d\rho/dE > 0$  for  $p_s > p_c$  [4,7,14–17]. The physical origin of this observation is an open question. Irrespective of the possible microscopic explanations of the  $\rho(E, p_s)$  dependence [14,18], a QPT implies that  $\rho$  scales with  $E$  if it scales with  $T$  [19]: close to the critical point, two characteristic length scales are associated with  $T$  and  $E$ ,  $L_\Phi(T) \sim T^{-1/z}$  and  $L_E(E) \sim E^{-1/(z+1)}$ , and  $\rho$  depends only on the ratio of the smallest of them to the correlation length  $\xi \sim |\delta_n|^{-\nu}$  ( $z$  is the dynamical exponent,  $\nu$

the correlation length exponent, and  $\delta_n = (p_s - p_c)/p_c$ ). Thus  $\rho(T, p_s)$  (for  $E \rightarrow 0$ ) depends only on  $|\delta_n|/T^{1/z\nu}$  on each side of the transition, and  $\rho(E, p_s)$  (at low temperature) depends only on  $|\delta_n|/E^{1/(z+1)\nu}$ . The scaling analysis of  $\rho(T, p_s)$  and  $\rho(E, p_s)$  allows a separate extraction of  $z$  and  $\nu$ .  $E$  scaling has been observed in several systems exhibiting  $T$  scaling [7,15–17]. However, a natural question is whether the  $\rho(E)$  dependence results from carrier heating [19]. At low temperature, the weak carrier-phonon coupling can lead to an effective temperature of the carriers,  $T_e(E)$ , larger than the lattice temperature  $T_l$  [9,20–28]. Thus, the  $\rho(E)$  dependence can be due to the  $T_e(E)$  dependence of  $\rho$ .

In this paper, we demonstrate experimentally that for a 2D hole system in  $p$ -SiGe exhibiting the MIT features with  $T$  and  $E$  scaling, the resistivity vs.  $E$ -field dependence can be attributed to hole heating. We find  $\rho(E, p_s) = \rho(T = T_e(E), p_s)$  with a law  $T_e(E)$  compatible both in shape and magnitude with known electron-phonon coupling models and data. The same  $T_e(E)$  is obtained from the damping of the Shubnikov-de Haas (SdH) oscillations. Thus, in the present case, the  $\rho(E, p_s)$  dependencies and the  $E$ -field “scaling” are not arguments in favor of the QPT interpretation of the “MIT” and the separate extraction of  $\nu$  and  $z$  is not possible. As heating effects depend on the semiconductor structure, while  $E$  scaling is a crucial issue for the QPT, we discuss the conditions required to study it for various systems in spite of carrier heating. We show how the ratio  $L_\Phi/L_E$  can be obtained experimentally.

The experiments were performed on  $\text{Si}_{0.85}\text{Ge}_{0.15}$  quantum wells sandwiched between undoped Si layers [7,12]. The 2D hole gas was formed in the triangular potential well at the Si/SiGe interface located on the boron doped side. It occupies the lowest heavy-hole subband, with an effective mass of about  $0.25m_0$ . Two gated Hall bars (S1

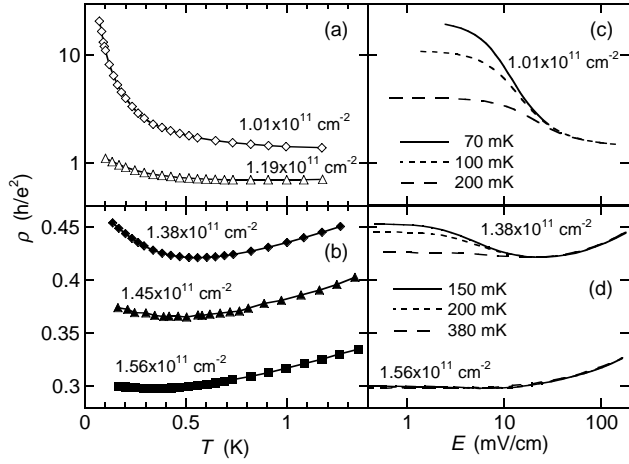


FIG. 1. (a)-(b) Resistivity as a function of temperature (for  $E \rightarrow 0$ ), at different densities for sample S1. (c)-(d) Resistivity as a function of electric field for various densities and lattice temperatures.

and S2) were used. Their width  $W$  is  $100 \mu\text{m}$ , and their length  $L$  (between voltage probes)  $233 \mu\text{m}$  for S1, and  $125 \mu\text{m}$  for S2. By varying the gate voltage, their densities can be tuned between  $0.50$  and  $1.75 \times 10^{11} \text{ cm}^{-2}$ . The mobilities at  $200 \text{ mK}$  increase with  $p_s$  from  $600$  to  $5500 \text{ cm}^2/\text{Vs}$  (resp.  $1000$  to  $7400 \text{ cm}^2/\text{Vs}$ ) for S1 (resp. S2). An ungated sample, with a density of  $3.9 \times 10^{11} \text{ cm}^{-2}$  and a mobility of  $7800 \text{ cm}^2/\text{Vs}$  has also been used. The temperature range was  $70 \text{ mK} - 1.4 \text{ K}$ . To check that the temperature  $T$  given by the thermometer fixed in the copper sample holder was that of the lattice  $T_l$ , the low current resistance of another Hall bar etched onto the same substrate was used as a thermometer. Its temperature remained close to  $T$  whatever the current in our samples.  $\rho = (V/I)(W/L)$  and  $E = V/L$  were obtained from the current  $I$  and the voltage drop  $V$  between the voltage probes, using a four point DC technique, with a current ( $10 - 300 \text{ pA}$  for low  $E$  measurements) periodically reversed at a frequency  $0.03 - 0.3 \text{ Hz}$ .

The MIT features appear in the  $\rho(T, p_s)$  dependence for  $E \rightarrow 0$  [Fig. 1(a)-(b)].  $d\rho/dT < 0$  is found for  $p_s < p_c \approx 1.3 \times 10^{11} \text{ cm}^{-2}$  ( $r_s \approx 6$ ), while  $d\rho/dT > 0$  for  $p_s > p_c$ , at temperatures above a threshold which decreases when  $p_s$  increases. At the largest densities  $d\rho/dT$  is positive. The  $\rho(T, p_s)$  data plotted as a function of  $|\delta_n|/T^b$  for  $T > 0.3 - 0.5 \text{ K}$  collapse on two branches (not shown), demonstrating a scaling behavior with  $b = 0.45 \pm 0.04$ . The values  $0.35$  [7] and  $0.62$  [5,6] were found in  $p$ -SiGe. The MIT characteristics and  $E$ -field scaling appear also in the  $\rho(E, p_s)$  curves (Fig. 2),  $p_c$  remaining unchanged. When  $\rho$  is plotted as a function of  $|\delta_n|/E^a$  ( $a = 0.19 \pm 0.02$ ), the curves fall on two branches (inset of Fig. 2). They contain only a part of the data (symbols on Fig. 2): removing the low  $E$  points is justified by  $L_E < L_\Phi$  (assuming a real QPT), while for

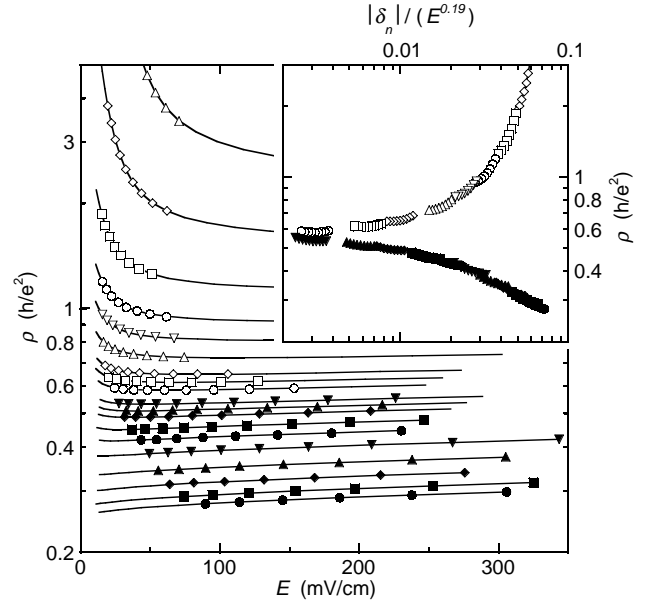


FIG. 2. Resistivity of sample S1 as a function of electric field at various hole densities: from  $p_s = 0.92 \times 10^{11} \text{ cm}^{-2}$  (top curve), to  $p_s = 1.75 \times 10^{11} \text{ cm}^{-2}$  (bottom curve). The lattice temperature is  $120 \text{ mK}$ . The lines give the whole set of data for  $E > 10 \text{ mV/cm}$ , while the symbols correspond to the fraction of the data used in the curves presented in the inset. Inset: resistivity as a function of  $|\delta_n|/E^{0.19}$ .

large  $E$ , it can be related to a microscopic limit on  $L_E$ .

Figure 1 shows that the general shape and the minima of  $\rho(E)$  are the same as those of  $\rho(T)$ , suggesting hot hole effects. Their contribution is studied as follows: (i) the  $\rho(E)$  dependence is assumed to result from the hole temperature rise from  $T_l$  to  $T_e$  due to Joule heating; (ii) for each value of  $E$ ,  $\rho$  is used as a “thermometer” giving  $T_e$  as the temperature  $T$  at which the same value of  $\rho$  is measured for  $E \rightarrow 0$ ; (iii) the relationship between  $T_e$  and the power per carrier  $P_E = VI/(p_s WL) = E^2/(\rho p_s)$  is used to study the validity of the hot carrier assumption (i). Figure 3(a) shows the  $P_E(T_e)$  dependence for various lattice temperatures and for densities around  $p_c$ .

The power loss between a degenerate 2D electron system and the lattice 3D acoustic phonons is given by [20]

$$P_E = A(T_e^\alpha - T_l^\alpha) + A'(T_e^{\alpha'} - T_l^{\alpha'}). \quad (1)$$

The first term corresponds to the deformation potential coupling, with  $\alpha = 5$  (resp.  $7$ ) for weak (resp. strong) screening. The second term is piezoelectric coupling, to be considered for our coherently strained SiGe samples [21,29], with  $\alpha' = 3$  (resp.  $5$ ) for weak (resp. strong) screening. The exponents may be decreased by one in disordered systems because of “dynamic” rather than “static” screening [23].  $A$  and  $A'$  are prefactors related to the deformation ( $\Xi_u$ ) and piezoelectric ( $e_{pz}$ ) coupling constants [20,21]. To test the validity of Eq. (1) for our measurements, we write it:  $P_E + (AT_l^\alpha + A'T_l^{\alpha'}) =$

$(AT_e^\alpha + A'T_e^{\alpha'})$ . Figure 3(b) shows that by adding to  $P_E$  a constant  $P_0(T_l)$  chosen separately for each  $T_l$ , the whole set of curves for a given density falls on the same master curve. Hence  $P_E(T_e, T_l) + P_0(T_l)$  depends only on  $T_e$ , and this dependence is the sum of two power laws. We have verified that the  $P_0(T_l)$  dependence is *the same*, thus proving that our data are in agreement with Eq. (1). Similar results are obtained for all densities and samples. For  $p_s$  close to  $p_c$ , a power law with  $\alpha' \approx 3$  (resp.  $\alpha \approx 5 - 6$ ) dominates at low (resp. large)  $T_e$ . These power laws are confirmed by fitting the  $P_E(T_e)$  data with Eq. (1). Fig. 3(a) shows the good quality of the fit when  $\alpha = 5$  and  $\alpha' = 3$  are imposed. For  $p_s > 1.35 \times 10^{11} \text{ cm}^{-2}$ , a term  $A''(T_e^2 - T_l^2)$  is added in the fit, corresponding to the cooling through the contacts which increases when  $\rho$  decreases [24].  $A''$  has the same order of magnitude as the value given by the Wiedeman-Franz law. Our data are thus compatible with Eq. (1), the two main cooling processes being hole-phonon coupling through weakly screened deformation and piezoelectric potentials. Weak screening at low temperatures has been pointed out in *p*-SiGe [21,26] and Si-MOSFETs [24,25].  $A$  and  $A'$  are obtained from a fit with Eq. (1) assuming  $\alpha = 5$  and  $\alpha' = 3$  [Fig. 3(a)]. Following Ref. [21] we then obtain  $\Xi_u = 2.7 \pm 0.3 \text{ eV}$  and  $e_{pz} = (3.4 \pm 0.9) \times 10^{-3} \text{ C/m}^2$  for all the densities. Our  $\Xi_u$  value is compatible with the  $\Xi_u \approx 3.0 \text{ eV}$  found in *p*-SiGe at  $p_s = (3.5 - 13) \times 10^{11} \text{ cm}^{-2}$  [21,26]. Our  $e_{pz}$  is somewhat lower than the  $e_{pz} \approx 1.6 \times 10^{-2} \text{ C/m}^2$  obtained in *p*-Si<sub>0.8</sub>Ge<sub>0.2</sub> [21], however in Ref. [26]  $e_{pz}$  was found to be much smaller than in Ref. [21].

In order to further prove the validity of the heating analysis, the  $T_e$  extracted at  $B = 0$  is compared to the temperature obtained using the damping of the SdH oscillations [21,22,24,27]. To get rid of the  $\rho_{xx}(T)$  dependence due to carrier scattering [27], the “thermometer” is the difference between a minimum of  $\rho_{xx}(B)$  and the previous maximum. Its  $T$  dependence results from a different physical situation (the density of states oscillations) than at  $B = 0$ . The magnetic field values ( $B \approx 1 \text{ T}$ ) are low to ensure that the electron-phonon coupling laws extracted are close to those at  $B = 0$  [27]. As shown in the inset of Fig. 3(a) for  $p_s = 1.19 \times 10^{11} \text{ cm}^{-2}$  and  $T_l = 150 \text{ mK}$ , the two methods are in very good agreement. A similar agreement is obtained for other  $T_l$  values and for  $p_s = 3.9 \times 10^{11} \text{ cm}^{-2}$ . Thus, the  $\rho(E)$  dependence can be attributed to hole heating, implying that it does not bring new physical information on the possible MIT when compared to the  $\rho(T)$  dependence.

To study  $E$ -field scaling in spite of heating effects, the condition  $L_E(E) < L_\Phi[T_e(E)]$  must be fulfilled. Figure 4 shows how  $L_\Phi$  and  $L_E$  depend on  $E$ . The vertical scale is arbitrary because  $L_\Phi$  and  $L_E$  are not given by the QPT theory, but assuming  $z = 1$  for strongly interacting particles [19],  $L_\Phi \sim T^{-1}$  and  $L_E \sim E^{-1/2}$ . Although the “metallic”  $\rho(T)$  in our samples is compatible with

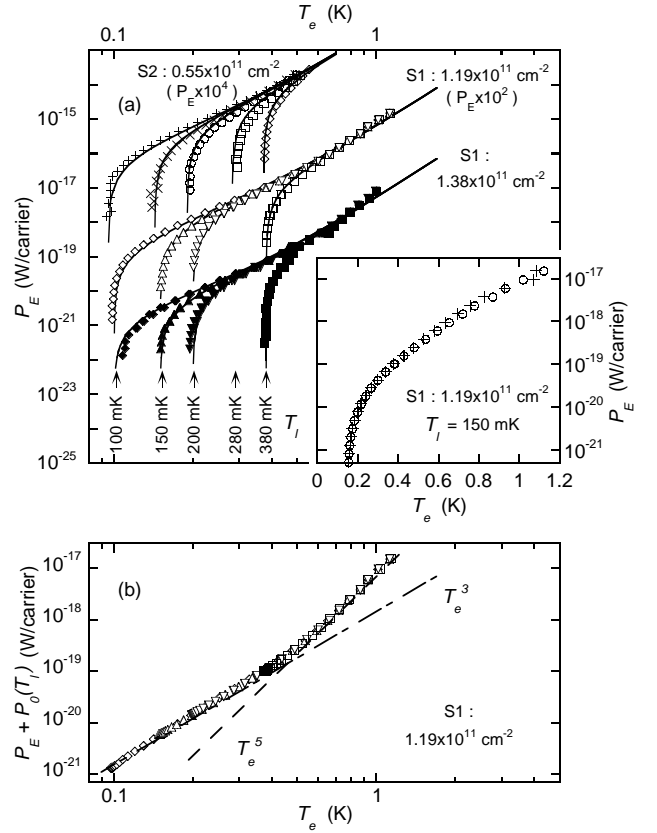


FIG. 3. (a) Power per hole injected in the 2D system as a function of the holes effective temperature, for two gated samples and three densities, at several lattice temperatures (arrows). For clarity, the curves corresponding to  $p_s = 1.19 \times 10^{11} \text{ cm}^{-2}$  (resp. to  $p_s = 0.55 \times 10^{11} \text{ cm}^{-2}$ ) are shifted upwards by 100 (resp. by  $10^4$ ). The lines corresponding to the two lower densities are fits to  $P_E = A(T_e^5 - T_l^5) + A'(T_e^3 - T_l^3)$ ; while for the larger density a third term  $A''(T_e^2 - T_l^2)$  has been added in the fit formula. Inset:  $P_E$  as a function of the effective temperature extracted using the  $\rho$  thermometer at  $B = 0$  (o) or the damping of the SdH oscillations (+). (b) The sum of the power per hole and a constant  $P_0(T_l)$  chosen for each  $T_l$ , as a function of the hole effective temperature, for various lattice temperatures  $T_l = 100 \text{ mK}$  ( $\diamond$ ),  $150 \text{ mK}$  ( $\triangle$ ),  $200 \text{ mK}$  ( $\nabla$ ), and  $380 \text{ mK}$  ( $\square$ ). The lines give the slopes of the power laws  $T_e^3$  and  $T_e^5$ .

a Fermi liquid description [12], it is instructive to consider the possibility of a QPT: the full line corresponds to  $L_\Phi[T_e(E)]$  in our case, for  $p_s \approx p_c$ , using the experimental law  $T_e(E)$ , obtained in the  $E$  interval indicated by the symbols. An upper limit for  $E$  arises since the longitudinal potential drop  $V = EL$  has to be kept small compared to the gate voltage. As we attributed the measured  $\rho(E)$  dependence to heating, the  $L_E(E)$  line (long dashed) crosses the  $L_\Phi[T_e(E)]$  curve beyond this interval. The  $E$ -field scaling can be investigated only beyond this crossing point, (“ $E$  scaling” interval in Fig. 4), provided  $L_\Phi$  and  $L_E$  do not reach their microscopic limit.

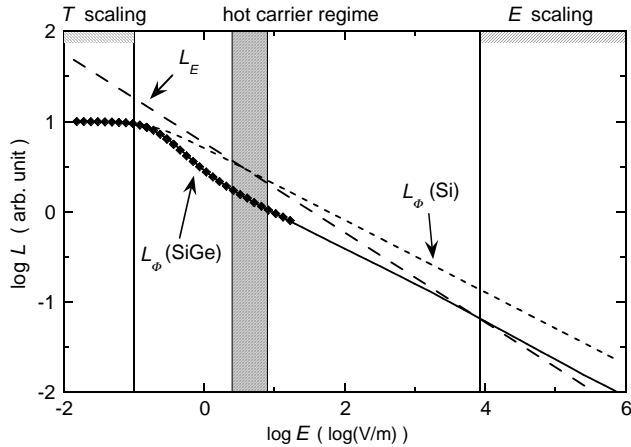


FIG. 4. The logarithm of  $L_\Phi$  and  $L_E$  as a function of the electric field. The full line represents  $L_\Phi[T_e(E)]$  calculated using Eq. (1) at  $p_s = 1.31 \times 10^{11} \text{ cm}^{-2}$  and  $T_l = 100 \text{ mK}$ . The symbols correspond to our experimental points. Short-dashed line:  $L_\Phi[T_e(E)]$  estimated for Si-MOSFETs close to the MIT. Long-dashed line:  $L_E(E)$  assumed to be the same for SiGe heterostructures and Si-MOSFETs. The vertical lines separate the hot carrier region from the  $T$  and  $E$  scaling regions for  $p$ -SiGe. The grey area gives the limits above which the  $E$ -field scaling is improved in Ref. [17]

The short dashed line in Fig. 4 is  $L_\Phi[T_e(E)]$  for Si-MOSFETs, estimated using recent measurements of the power loss [24,30]. Again, the  $L_E(E) < L_\Phi[T_e(E)]$  prescription leads to a lower limit for  $E$ . This agrees with the results of Ref. [17] where the quality of the  $E$ -field scaling is improved when  $E$  is larger than a minimum value (the grey area in Fig. 4, corresponds to their cut-offs of 50 to 500 pW). For  $p$ -GaAs, the  $\alpha = 5$  exponent quoted in Ref. [28] leads to a similar situation, but the thermal coupling should be larger than in Si-MOSFETs. Unscreened piezoelectric coupling would lead to an upper  $E$ -field limit. A better knowledge of the power loss laws would allow a quantitative use of the  $L_E(E) < L_\Phi(T_e)$  prescription. The field  $E_c$  defined by  $L_E(E_c) = L_\Phi[T_e(E_c)]$  could be extracted as the limit beyond which the experimental  $P_E(T_e)$  law differs from the power loss law, thus yielding the important physical result  $L_\Phi(T)/L_E(E) = [T_e(E_c)/T]^{1/z}(E/E_c)^{1/(z+1)}$ .

The ratio of the exponents in the experimental scaling laws  $\rho(|\delta_n|/T^b)$  and  $\rho(|\delta_n|/E^a)$  has been proposed as an indicator of the  $\rho(E)$  dependence origin [19]. For the QPT scaling,  $a/b = z/(z+1) = 0.5$ . For carrier heating, Eq. (1) gives  $T_e \sim (E^{2/\alpha})\rho^{-1/\alpha}$ , thus  $a/b = 2/\alpha$  neglecting  $A'$ ,  $T_l$  and the  $\rho(T)$  dependence. We find experimentally  $a/b = 0.42 \pm 0.08$ , while 0.4 and 0.67 are expected for our  $\alpha$  and  $\alpha'$ , thus the  $a/b$  criterion can hardly be used [31].

In summary, we have shown that in a 2D hole system exhibiting the  $B = 0$  MIT characteristics, with  $T$  and  $E$  scaling, the  $\rho(E)$  dependence close to the MIT could

be interpreted as being due to hole heating. Thus, in our case, the experimental  $\rho(E, p_s)$  and  $E$ -field scaling are not an indication that the MIT features can be attributed to a QPT, and the separate extraction of  $\nu$  and  $z$  is not possible. However, there is an  $E$  interval defined by  $L_E(E) < L_\Phi[T_e(E)]$  where  $E$ -field scaling can be investigated independent of hot carrier effects.

The authors thank T. Jolicoeur for helpful discussions.

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  - [30] The authors of Ref. [24] find  $P_E \approx 1.5 \times 10^6 n_s^{-3/2} (T_e^5 - T_l^5)$  ( $P_E$  in W,  $n_s$  in  $\text{m}^{-2}$ ), rather close to the result of Ref. [25]. We used this equation with  $n_s = 10^{15} \text{ m}^{-2}$ . For weak screening the conductivity dependence of the prefactor given in Ref. [23] should not be relevant.
  - [31] Similarly, in Si-MOSFETs, unscreened electron-phonon coupling [24,25] would lead to  $2/\alpha = 0.4$ .